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	Application No.	Applicant(s)
Notice of Allowability	10/743,629 Examiner	LEE, KI MIN Art Unit
	Examine:	
	David Nhu	2818
The MAILING DATE of this communication apperation apperation allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this app or other appropriate communication GHTS. This application is subject to	plication. If not included will be mailed in due course. THIS
1. X This communication is responsive to 6/6/05.		
2. The allowed claim(s) is/are <u>1-8</u> .		
3. \boxtimes The drawings filed on <u>22 December 2003</u> are accepted by	the Examiner.	
4. Acknowledgment is made of a claim for foreign priority una All b Some* c None of the: 1.	been received. been received in Application No cuments have been received in this of this communication to file a reply ENT of this application. itted. Note the attached EXAMINER bes reason(s) why the oath or declara of the submitted. con's Patent Drawing Review (PTO- s Amendment / Comment or in the Co state of BIOLOGICAL MATERIAL re	national stage application from the complying with the requirements 'S AMENDMENT or NOTICE OF tion is deficient. 948) attached Office action of the back) of d). must be submitted. Note the
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date	6. ☐ Interview Summary Paper No./Mail Dat 8), 7. ☐ Examiner's Amendr	te

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REASONS FOR ALLOWANCE

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- Claims 1-8 are allowed.
- The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests as cited in claims 1: depositing Ti/Ti_{$l\to 0$}Al_{κ}N as a first barrier metal layer on a bottom and sidewalls of the via hole by a plasma chemical vapor deposition (CVD); filling the via hole with a plug material to form a via plug; performing a planarization process to flatten the via plug; depositing a second barrier metal layer and a metal line in sequence on the substrate including the via plug; and depositing an ARC layer of Ti/Ti on the metal line by a plasma CVD.
- 3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

CONCLUSION

- 4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Horii (6,630,387 B2): Method for Forming Capacitor of Semiconductor Memory Device Using Electroplating Methods.
- 5. Any inquiry concerning this communication on earlier communications from the examiner should be directed to David Nhu, (571)272-1792. The examiner can normally be reached on Monday-Friday from 7:30 AM to 5:00 PM.

The examiner's supervisor, David Nelms can be reached on (571)272-1787.

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The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956

David Nhu

June 17, 2005

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